

SWITCHING REGULATOR APPLICATIONS

Features

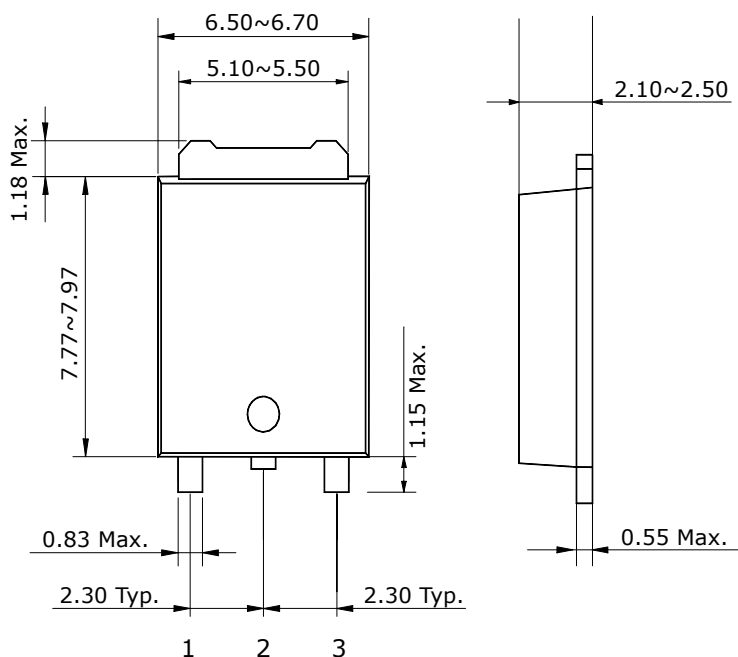
- High Voltage: $BV_{DSS}=600V(\text{Min.})$
- Low C_{rSS} : $C_{rSS}=4.3pF(\text{Typ.})$
- Low gate charge : $Qg=4.5nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=9.4\Omega(\text{Max.})$

Ordering Information

| Type NO. | Marking | Package Code |
|----------|---------|--------------|
| STK0160D | STK0160 | D-PAK |

Outline Dimensions

unit : mm



PIN Connections

1. Gate
2. Drain
3. Source

Absolute maximum ratings

(Tc=25°C)

| Characteristic | Symbol | Rating | Unit | |
|----------------------------------|-----------|------------|------|---|
| Drain-source voltage | V_{DSS} | 600 | V | |
| Gate-source voltage | V_{GSS} | ±30 | V | |
| Drain current (DC) | I_D | (Tc=25°C) | 1.0 | A |
| | | (Tc=125°C) | 0.70 | A |
| Drain current (Pulsed) * | I_{DP} | 4.0 | A | |
| Drain Power dissipation | P_D | 28 | W | |
| Avalanche current (Single) ② | I_{AS} | 1.0 | A | |
| Single pulsed avalanche energy ② | E_{AS} | 22 | mJ | |
| Avalanche current (Repetitive) ① | I_{AR} | 1.0 | A | |
| Repetitive avalanche energy ① | E_{AR} | 2.5 | mJ | |
| Junction temperature | T_J | 150 | °C | |
| Storage temperature range | T_{stg} | -55~150 | | |

* Limited by maximum junction temperature

| Characteristic | | Symbol | Typ. | Max | Unit |
|--------------------|------------------|---------------|------|------|------|
| Thermal resistance | Junction-case | $R_{th(J-C)}$ | - | 4.46 | °C/W |
| | Junction-ambient | $R_{th(J-a)}$ | - | 83.3 | |

Electrical Characteristics

(Tc=25°C)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit | |
|--------------------------------|--------------|---|------|------|-----------|----------|-----|
| Drain-source breakdown voltage | BV_{DSS} | $I_D=250\mu A, V_{GS}=0$ | 600 | - | - | V | |
| Gate-threshold voltage | $V_{GS(th)}$ | $I_D=250\mu A, V_{DS}=V_{GS}$ | 2.0 | - | 4.0 | V | |
| Drain-source leakage current | I_{DSS} | $V_{DS}=600V, V_{GS}=0V$ | - | - | 1 | μA | |
| Gate-source leakage | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 30V$ | - | - | ± 100 | nA | |
| Drain-Source on-resistance ④ | $R_{DS(on)}$ | $V_{GS}=10V, I_D=0.5A$ | - | 8.8 | 9.4 | Ω | |
| Forward transfer admittance ④ | g_{fs} | $V_{DS}=10V, I_D=0.5A$ | - | 0.95 | - | S | |
| Input capacitance | C_{iss} | $V_{GS}=0V, V_{DS}=25V, f=1MHz$ | - | 150 | 225 | pF | |
| Output capacitance | C_{oss} | | - | 20 | 30 | | |
| Reverse transfer capacitance | C_{rss} | | - | 4.3 | 6.4 | | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=300V, V_{GS}=10V$ $I_D=1.0A, R_G=25\Omega$ | - | 22.5 | - | ns | |
| Rise time | t_r | | - | 27 | - | | |
| Turn-off delay time | $t_{d(off)}$ | | ③④ | - | 11.5 | | - |
| Fall time | t_f | | - | 27 | - | | |
| Total gate charge | Q_g | $V_{DD}=300V, V_{GS}=10V$ $I_D=1.0A$ | - | 4.5 | 6.7 | nC | |
| Gate-source charge | Q_{gs} | | - | 0.9 | 1.3 | | |
| Gate-drain charge | Q_{gd} | | ③④ | - | 1.3 | | 1.9 |

Source-Drain Diode Ratings and Characteristics

(Tc=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|---------------------------|----------|--|-----|------|-----|---------|
| Continuous source current | I_S | Integral reverse diode in the MOSFET | - | - | 1.0 | A |
| Source current (Pulsed) ① | I_{SM} | | - | - | 4.0 | |
| Forward voltage ④ | V_{SD} | $V_{GS}=0V, I_S=1.0A$ | - | - | 1.4 | V |
| Reverse recovery time | t_{rr} | $I_S=1.0A, V_{GS}=0V$ $di_s/dt=100A/us$ | - | 160 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 0.59 | - | μC |

Note ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② $L=20mH, I_{AS}=1.0A, V_{DD}=50V, R_G=25\Omega$
- ③ Pulse Test : Pulse Width < 300us, Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

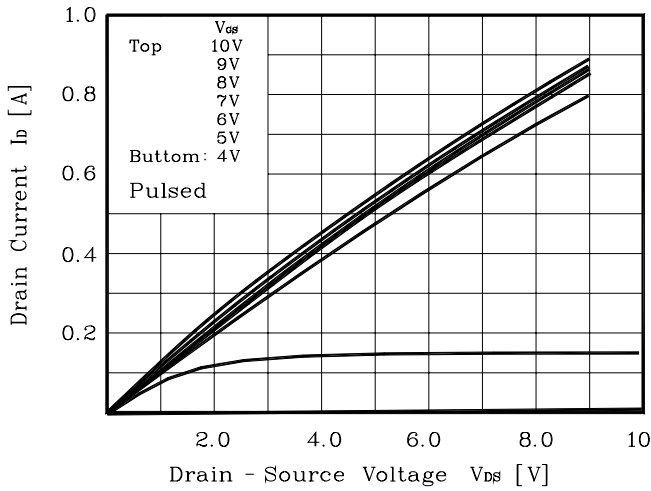


Fig. 2 $I_D - V_{GS}$

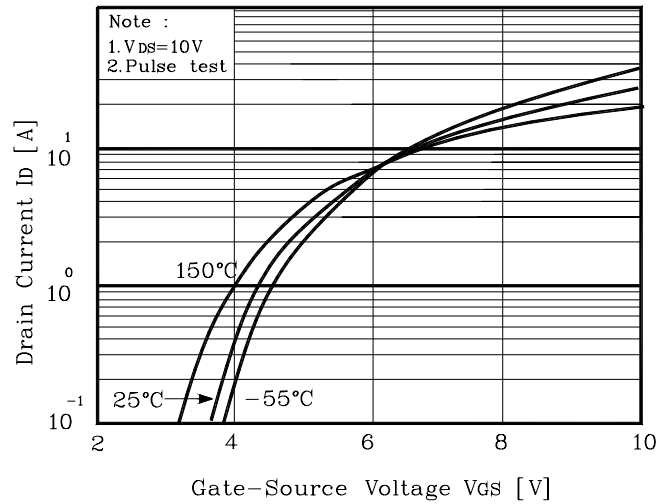


Fig. 3 $R_{DS(on)} - I_D$

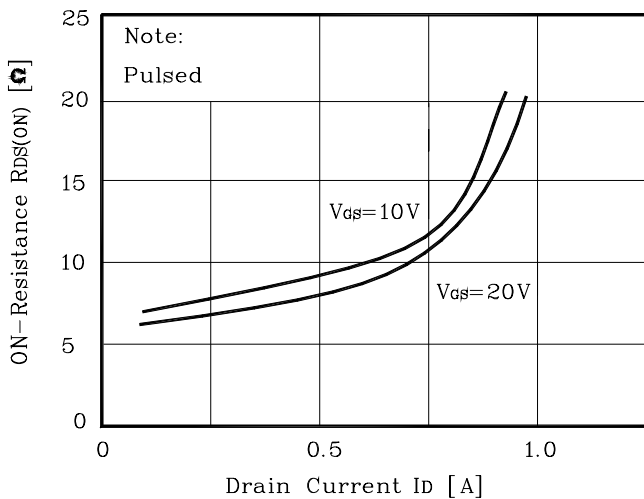


Fig. 4 $I_S - V_{SD}$

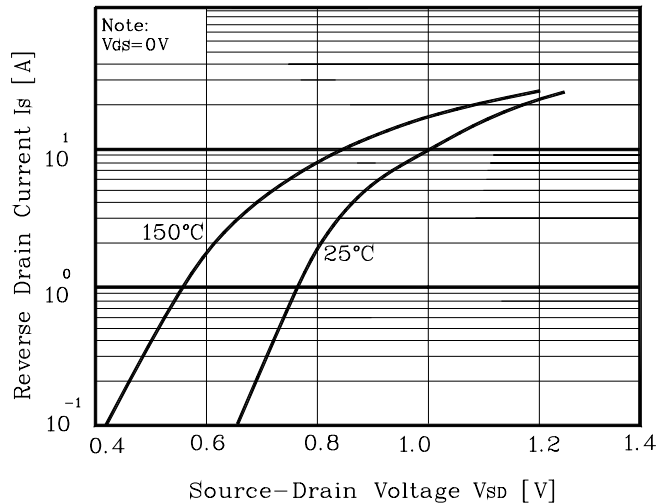


Fig. 5 Capacitance - V_{DS}

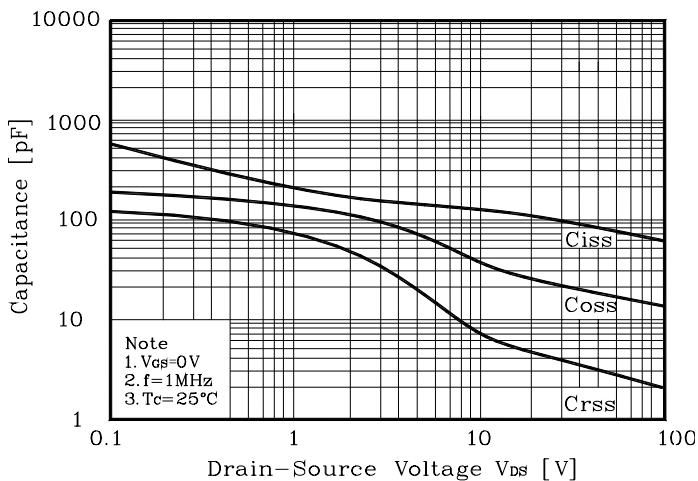


Fig. 6 $V_{GS} - Q_G$

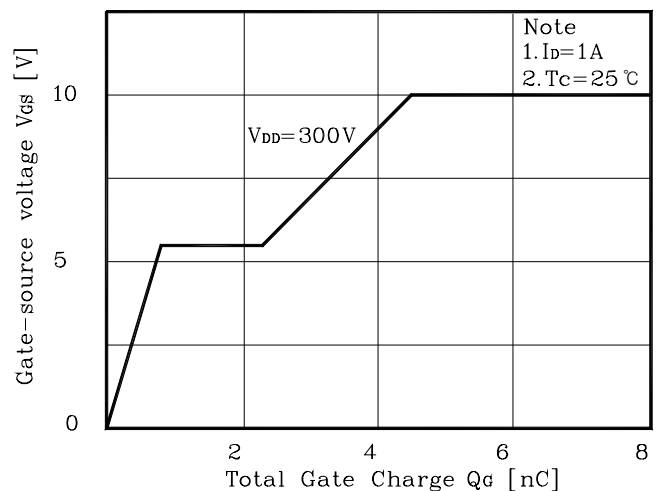


Fig. 7 $V_{DSS} - T_J$

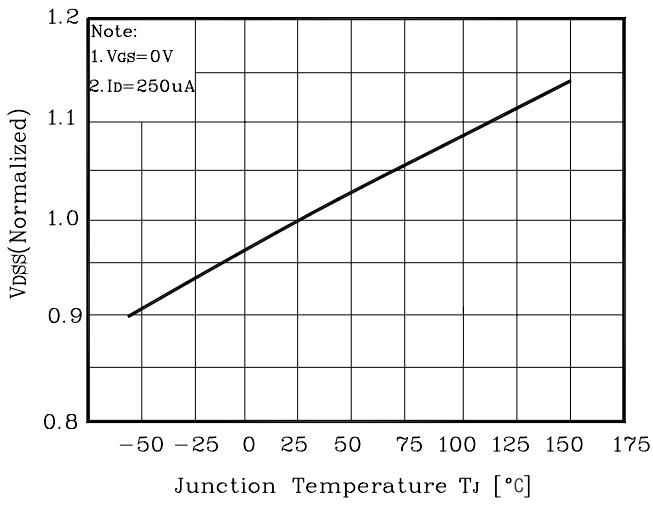


Fig. 8 $R_{DS(on)} - T_J$

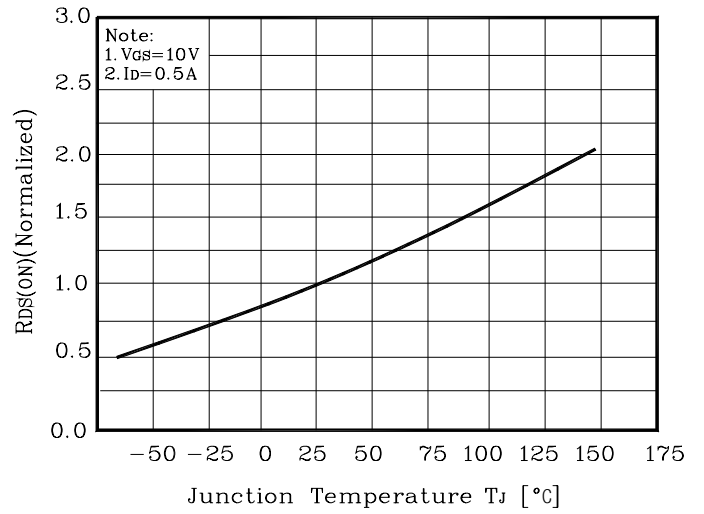


Fig. 9 $I_D - T_C$

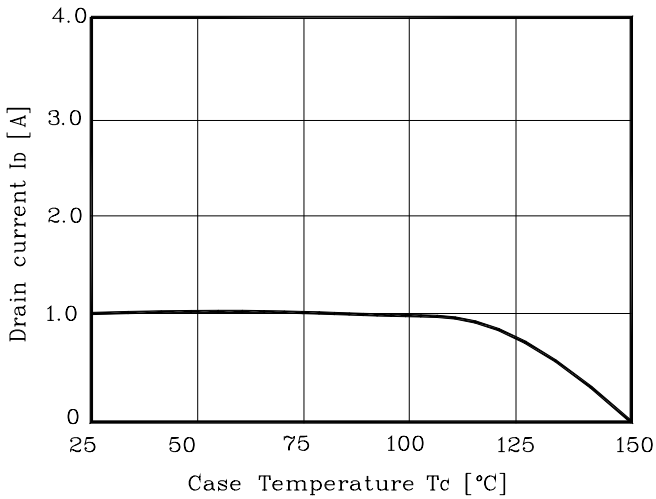


Fig. 10 Safe Operating Area

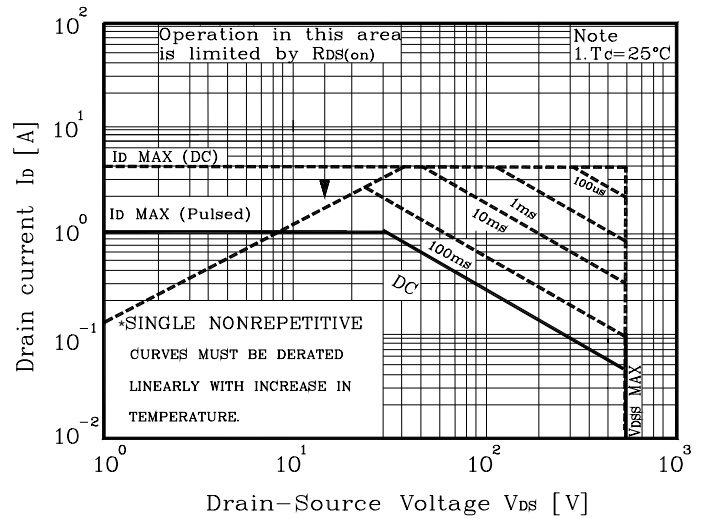


Fig. 11 Gate Charge Test Circuit & Waveform

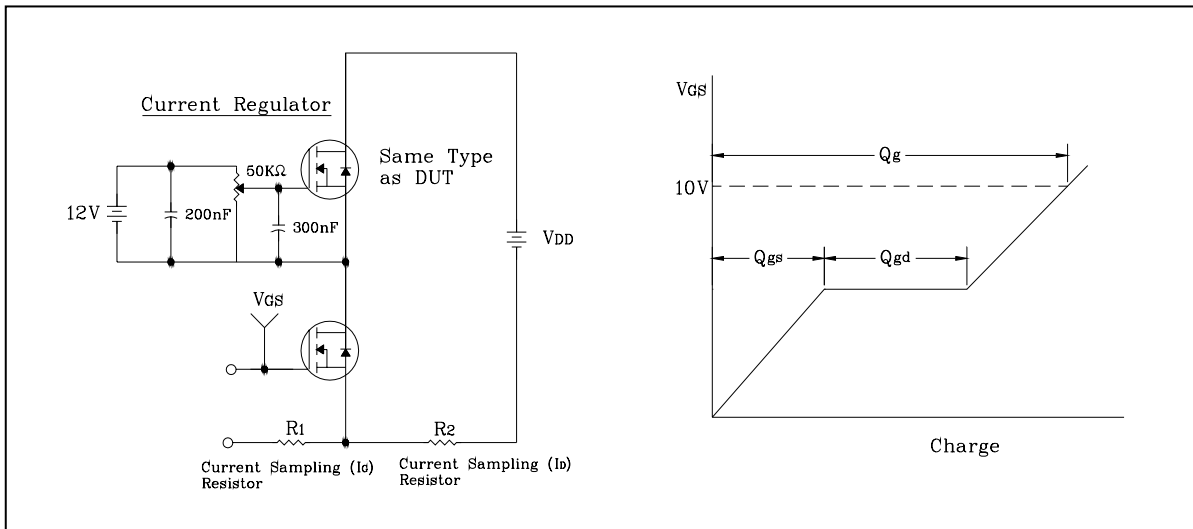


Fig. 12 Resistive Switching Test Circuit & Waveform

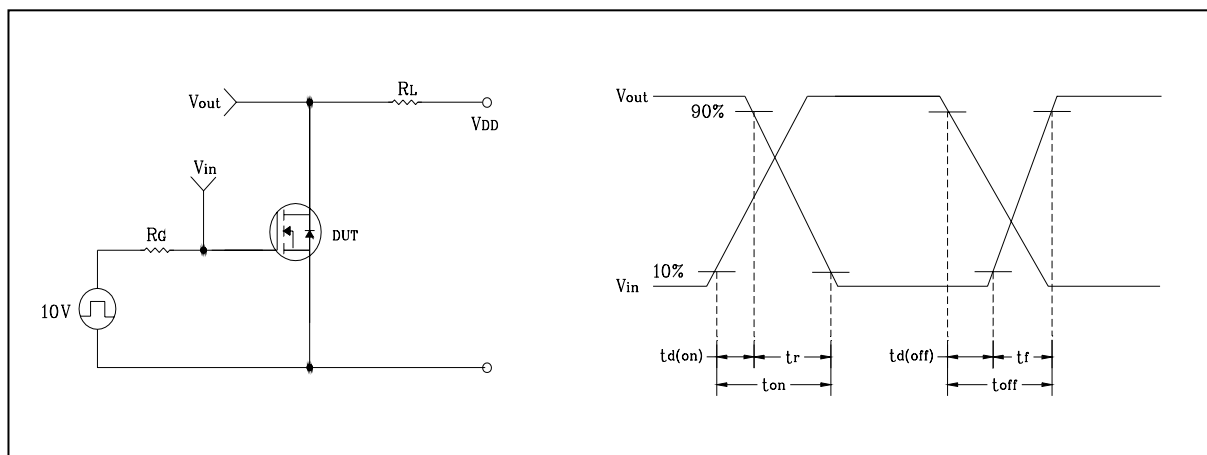


Fig. 13 EAS Test Circuit & Waveform

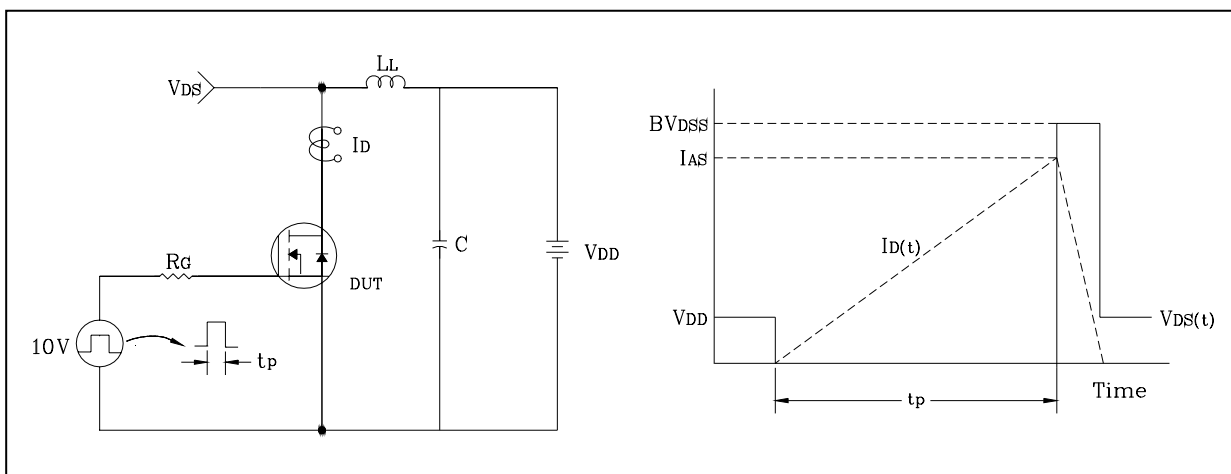
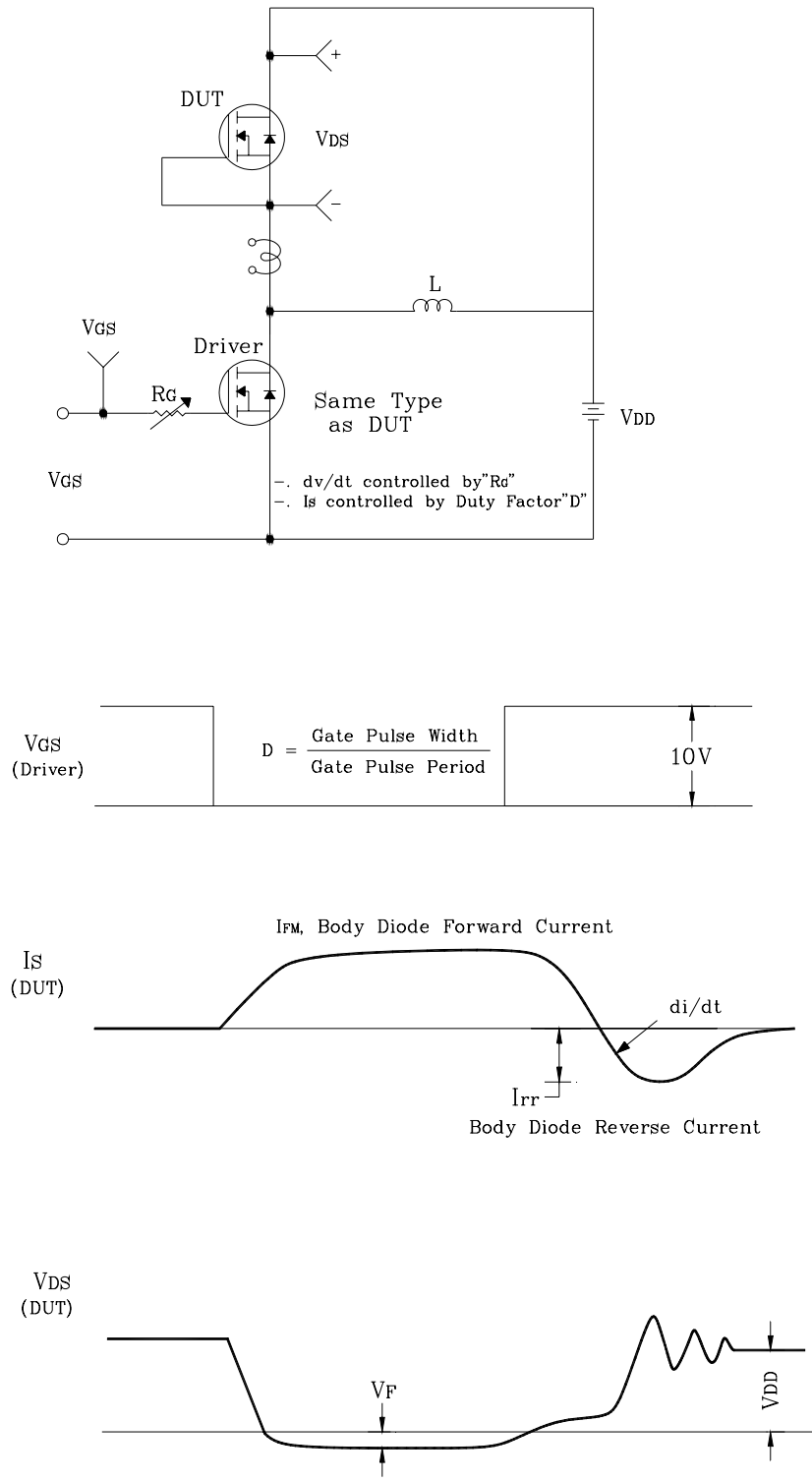


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



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